



N-Channel 30-V (D-S) 175°C MOSFET

PRODUCT SUMMARY

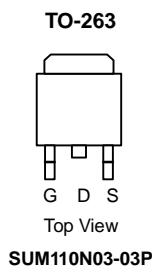
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a
30	0.0026 @ $V_{GS} = 10$ V	110 ^a
	0.004 @ $V_{GS} = 4.5$ V	110 ^a

FEATURES

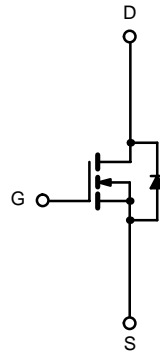
- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- Optimized for Low-Side Synchronous Rectifier

APPLICATIONS

- Desktop or Server CPU Core



DRAIN connected to TAB



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	110 ^a	
		$T_C = 100^\circ\text{C}$	110 ^a	
Pulsed Drain Current	I_{DM}	400	A	
Avalanche Current	I_{AR}	65		
Repetitive Avalanche Energy ^b	E_{AR}	L = 0.1 mH	211	mJ
Maximum Power Dissipation ^b			$T_C = 25^\circ\text{C}$ (TO-220AB and TO-263)	375 ^c
	$T_A = 25^\circ\text{C}$ (TO-263) ^d	3.75		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	PCB Mount (TO-263) ^d	40
		Free Air (TO-220AB)	62.5
Junction-to-Case	R_{thJC}	0.4	$^\circ\text{C}/\text{W}$

Notes

- Package limited.
- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

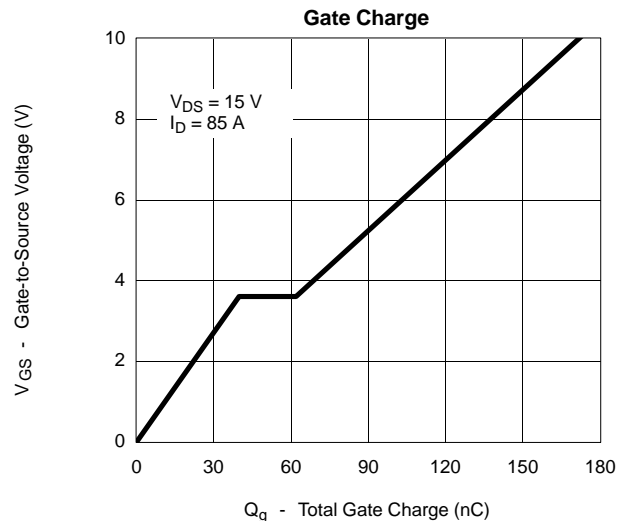
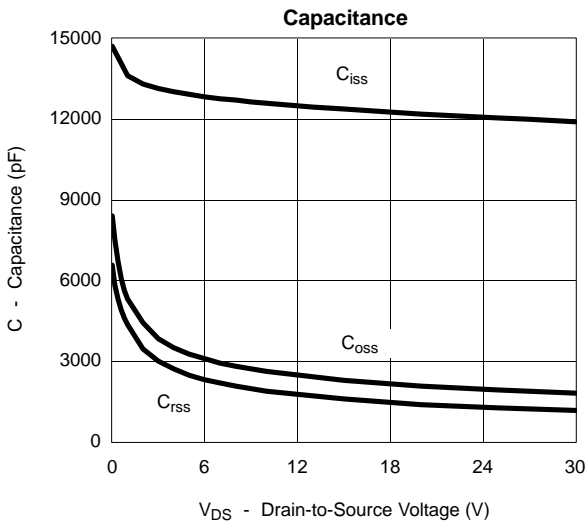
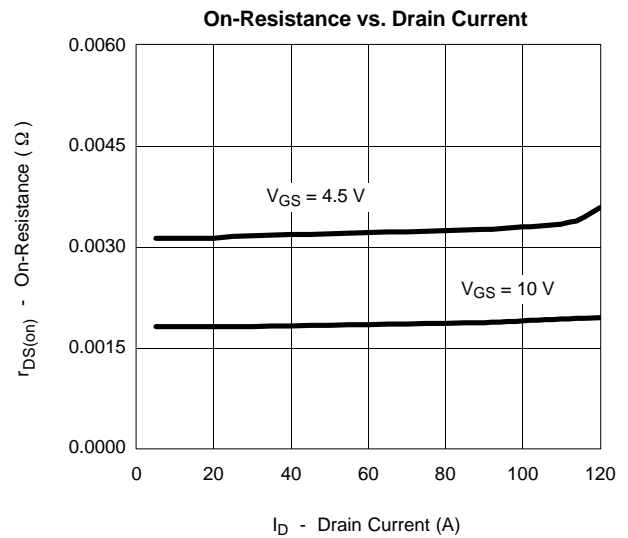
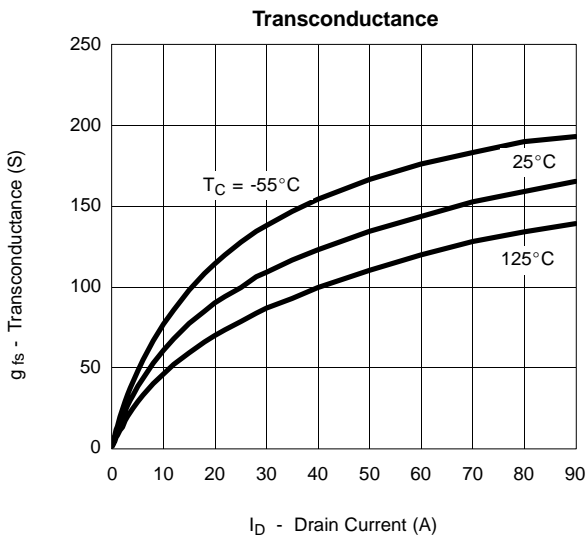
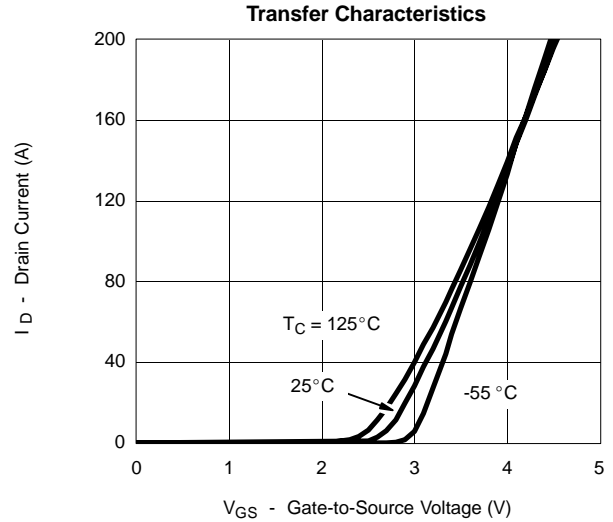
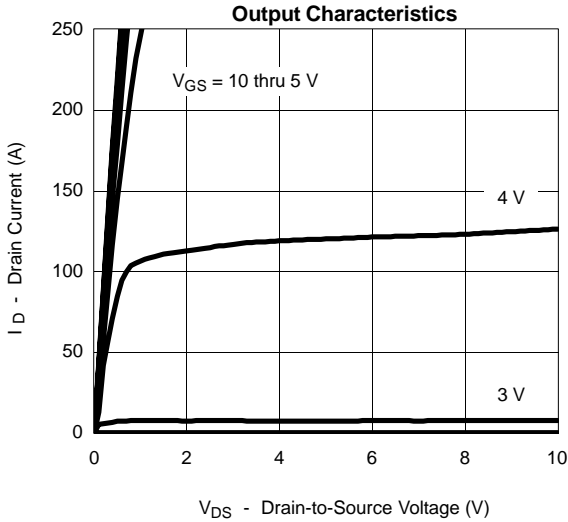
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	30			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1	2	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.002	0.0026	Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.004	
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C			0.005	
		V _{GS} = 4.5 V, I _D = 20 A		0.0031	0.004	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	20			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		12100		pF
Output Capacitance	C _{oss}			1910		
Reverse Transfer Capacitance	C _{rss}			1250		
Total Gate Charge ^b	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 110 A		172	250	nC
Gate-Source Charge ^b	Q _{gs}			40		
Gate-Drain Charge ^b	Q _{gd}			22		
Gate Resistance	R _G			1.3		Ω
Turn-On Delay Time ^b	t _{d(on)}	V _{DD} = 15 V, R _L = 0.18 Ω I _D = 110 A, V _{GEN} = 10 V, R _G = 2.5 Ω		20	35	ns
Rise Time ^b	t _r			20	35	
Turn-Off Delay Time ^b	t _{d(off)}			90	140	
Fall Time ^b	t _f			25	40	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^c						
Continuous Current	I _S				85	A
Pulsed Current	I _{SM}				440	
Forward Voltage ^a	V _{SD}	I _F = 110 A, V _{GS} = 0 V		1.1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 85 A, di/dt = 100 A/μs		60	120	ns
Peak Reverse Recovery Current	I _{RM}			3.5	5	A
Reverse Recovery Charge	Q _{rr}			0.1	0.3	μC

Notes

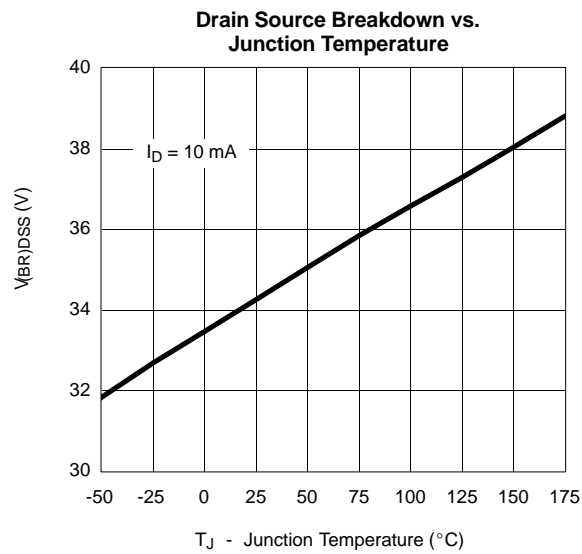
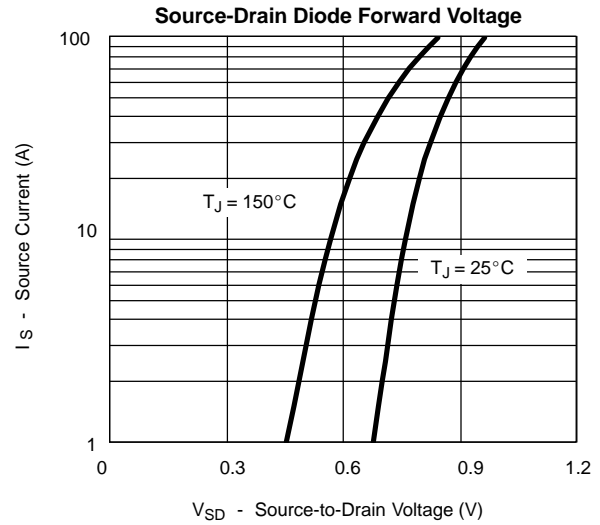
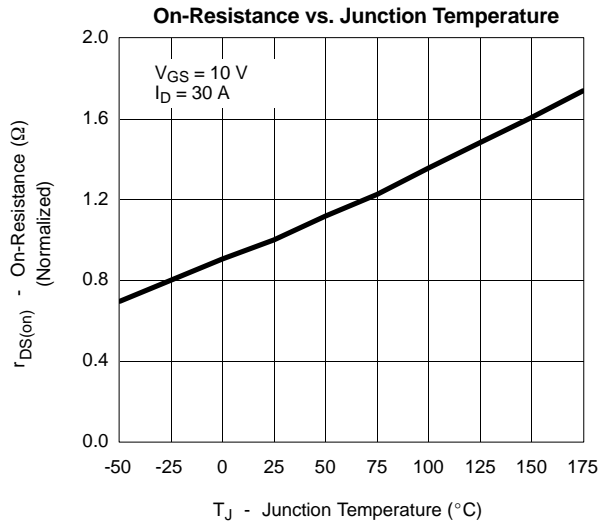
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.
- Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



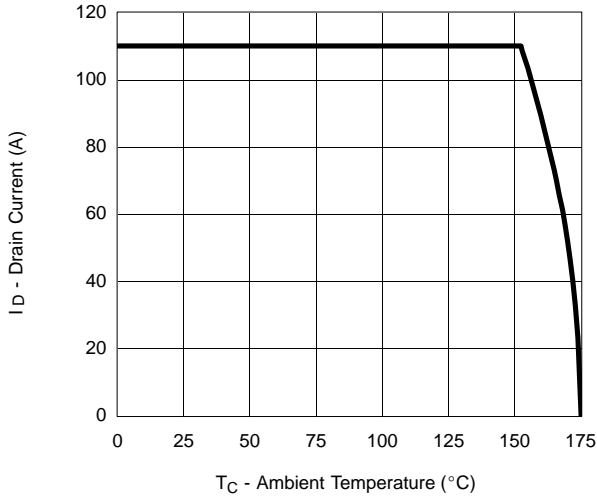
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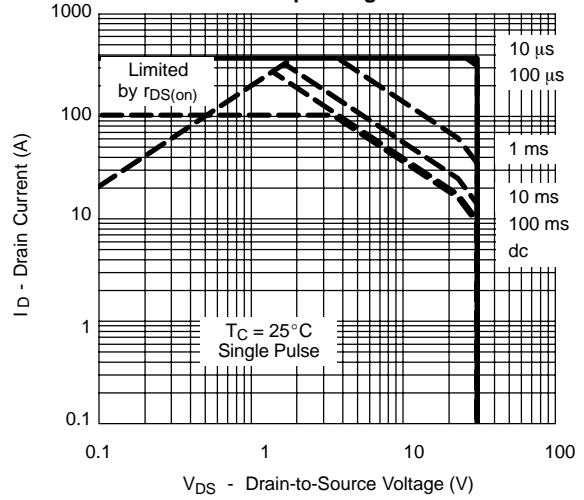


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

